



#### 20V N-Channel Enhancement Mode MOSFET

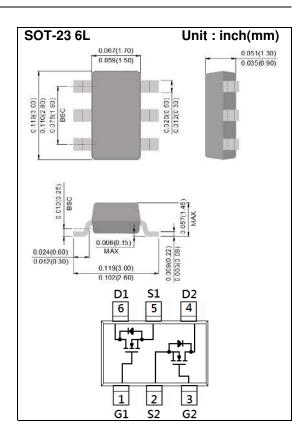
Voltage 20 V Current 5.2A

#### **Features**

- RDS(ON) , VGS@4.5V, ID@5.2A<29mΩ</li>
- RDS(ON) , VGS@2.5V, ID@3.7A<42mΩ</li>
- RDS(ON), VGS@1.8V, ID@1.6A<85mΩ
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

- Case: SOT-23 6L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0005 ounces, 0.014 grams
- Marking: S16



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	20	V
Gate-Source Voltage		$V_{GS}$	<u>+</u> 12	V
Continuous Drain Current		ID	5.2	Α
Pulsed Drain Current		I <sub>DM</sub>	20.8	Α
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	1.25	W
	Derate above 25°C		10	mW/°C
Operating Junction and Storage Temperature Range		$T_{J},T_{STG}$	-55~150	°C
Typical Thermal Resistance - Junction to Ambient <sup>(Note 3)</sup>		R <sub>θ</sub> ЈА	100	°C/W





## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.5	0.77	1.2	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =5.2A	-	26	29	mΩ	
		$V_{GS}$ =2.5V, $I_{D}$ =3.7A	-	35	42		
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =1.6A	-	62	85		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	0.01	1	uA	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 12V, V <sub>DS</sub> =0V	-	<u>+</u> 10	<u>+</u> 100	nA	
Dynamic							
Total Gate Charge	$Q_g$	V <sub>DS</sub> =10V, I <sub>D</sub> =5.2A,	-	7	-	nC	
Gate-Source Charge	$Q_gs$		-	1.3	-		
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	2	-		
Input Capacitance	Ciss	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V,	-	513	-	pF	
Output Capacitance	Coss		-	74	-		
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	60	-		
Switching							
Turn-On Delay Time	td <sub>(on)</sub>	$\begin{array}{c} V_{DD}{=}10V,\ I_{D}{=}5.2A, \\ V_{GS}{=}4.5V, \\ R_{G}{=}6\Omega^{(Note\ 1,2)} \end{array}$	-	6.2	-	ns	
Turn-On Rise Time	tr			56			
Turn-Off Delay Time	td <sub>(off)</sub>		-	23	-		
Turn-Off Fall Time	tf		-	13	-		
Drain-Source Diode							
Maximum Continuous Drain-Source Diode Forward Current	ls		-	-	1.5	Α	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V	_	0.71	1.2	V	

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
- 4. The maximum current rating is package limited





#### **TYPICAL CHARACTERISTIC CURVES**

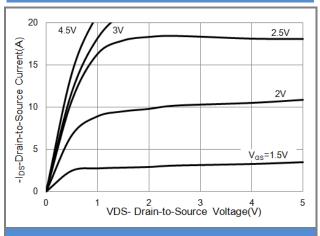


Fig.1 On-Region Characteristics

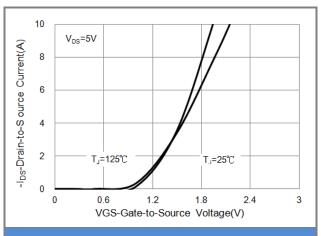


Fig.2 Transfer Characteristics

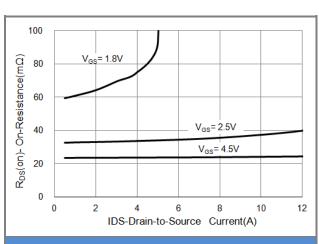


Fig.3 On-Resistance vs. Drain Current

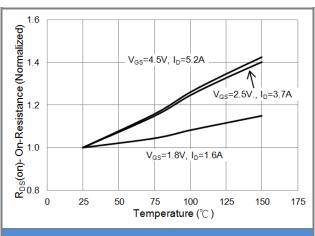


Fig.4 On-Resistance vs. Junction temperature

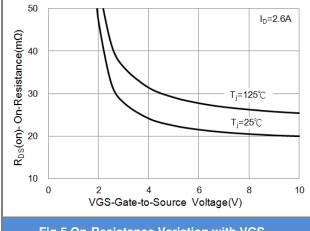
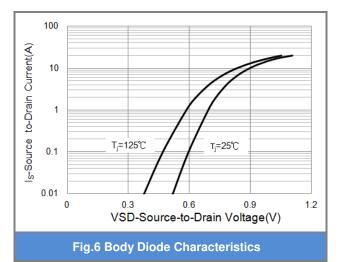


Fig.5 On-Resistance Variation with VGS.

January 20,2022







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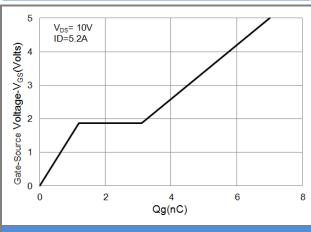


Fig.7 Gate-Charge Characteristics

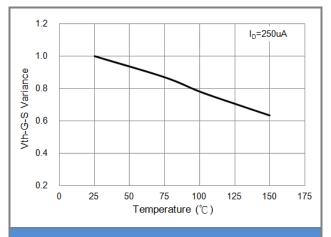
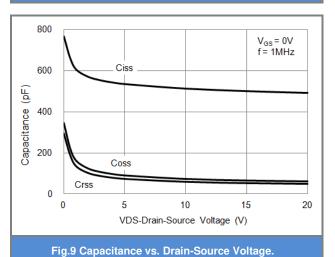


Fig.8 Threshold Voltage Variation with Temperature



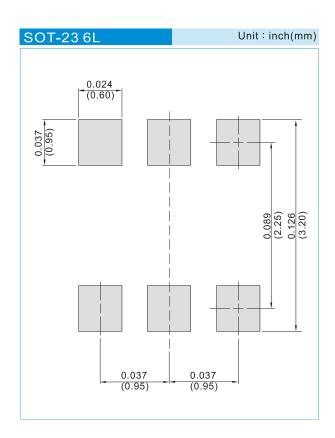




## PART NO. PACKING CODE VERSION

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJS6816_S1_00001	SOT-23 6L	3K pcs / 7" reel	SE6	Halogen free RoHS compliant
PJS6816_S2_00001	SOT-23 6L	10K pcs / 13" reel	SE6	Halogen free RoHS compliant

## **MOUNTING PAD LAYOUT**







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